

TS4902

300mW at 3.3V SUPPLY AUDIO POWER AMPLIFIER WITH STANDBY MODE ACTIVE LOW

OPERATING FROM V_{cc} = 2.2V to 5.5V

- **0.7W** OUTPUT POWER @ Vcc=5V, THD=1%, f=1kHz, with an 8Ω load
- **0.3W** OUTPUT POWER @ Vcc=**3.3**V, THD=1%, f=1kHz, with an **8**Ω load
- ULTRA LOW CONSUMPTION IN STANDBY MODE (10nA)
- **77dB** PSRR @ 217Hz from 5V to 2.2V
- ULTRA LOW POP & CLICK
- ULTRA LOW DISTORTION (0.1%)
- UNITY GAIN STABLE
- AVAILABLE IN MiniSO8 & SO8

DESCRIPTION

The TS4902 is an audio power amplifier designed to provide the best price to power ratio while preserving high audio quality.

Available in MiniSO8 & SO8 package, it is capable of delivering up to 0.7W of continuous RMS ouput power into an 8Ω load @ 5V.

TS4902 is also exhibiting an outstanding 0.1% distortion level (THD) from a 5V supply for a Pout of 200mW RMS.

An externally controlled standby mode reduces the supply current to less than 10nA. It also includes an internal thermal shutdown protection.

The unity-gain stable amplifier can be configured by external gain setting resistors.

APPLICATIONS

Mobile Phones (Cellular / Cordless)
PDAs
Portable Audio Devices

ORDER CODE

Part Number	Temperature	Pacl	kage
Fait Nulliber	Range	ST	D
TS4902IST	10 J95°C	٠	
TS4902ID	-40, + 65 C		•

 ${\bf S}$ = MiniSO Package (MiniSO) is only available in Tape & Reel (ST) ${\bf D}$ = Small Outline Package (SO) - also available in Tape & Reel (DT)

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PIN CONNECTIONS (top view)



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{CC}	Supply voltage ¹⁾	6	V
Vi	Input Voltage ²⁾	G_{ND} to V_{CC}	V
T _{oper}	Operating Free Air Temperature Range	-40 to + 85	°C
T _{stg}	Storage Temperature	-65 to +150	°C
Тj	Maximum Junction Temperature	150	°C
R _{thja}	Thermal Resistance Junction to Ambient ³⁾ SO8 MiniSO8	175 215	°C/W
Pd	Power Dissipation ⁴⁾	See the power derating curves Fig 20.	
ESD	Human Body Model	2	kV
ESD	Machine Model	200	V
Latch-up	Latch-up Immunity	Class A	
	Lead Temperature (soldering, 10sec)	250	°C

1. All voltages values are measured with respect to the ground pin.

2. The magnitude of input signal must never exceed V_{CC} + 0.3V / G_{ND} - 0.3V

3. Device is protected in case of over temperature by a thermal shutdown active @ 150°C.

4. Exceeding the power derating curves during a long period, will cause abnormal operation.

OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V _{CC}	Supply Voltage	2.2 to 5.5	V
V _{ICM}	Common Mode Input Voltage Range	G _{ND} to V _{CC} - 1.5V	V
V _{STB}	Standby Voltage Input : Device ON Device OFF	$1.5 \le V_{STB} \le V_{CC}$ GND $\le V_{STB} \le 0.5$	V
RL	Load Resistor	4 - 32	Ω
R _{thja}	Thermal Resistance Junction to Ambient ¹⁾ SO8 MiniSO8	150 190	°C/W

1. This thermal resistance can be reduced with a suitable PCB layout (see Power Derating Curves)

ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Min.	Тур.	Max.	Unit
I _{CC}	Supply Current No input signal, no load		6	8	mA
I _{STANDBY}	Standby Current ¹⁾ No input signal, Vstdby = GND, RL = 8Ω		10	1000	nA
Voo	Output Offset Voltage No input signal, RL = 8Ω		5	20	mV
Ро	Output Power THD = 1% Max, f = 1kHz, RL = 8Ω		0.7		W
THD + N	Total Harmonic Distortion + Noise Po = 250mW rms, Gv = 2, 20Hz < f < 20kHz, RL = 8Ω		0.15		%
PSRR	Power Supply Rejection Ratio ²⁾ f = 217Hz, RL = 8 Ω , RFeed = 22K Ω , Vripple = 200mV rms		77		dB
Φ_{M}	Phase Margin at Unity Gain $R_L = 8\Omega$, $C_L = 500pF$		70		Degrees
GM	Gain Margin R _L = 8 Ω , C _L = 500pF		20		dB
GBP	Gain Bandwidth Product $R_L = 8\Omega$		2		MHz

 $V_{cc} = +5V$, GND = 0V, $T_{amb} = 25^{\circ}C$ (unless otherwise specified)

1. Standby mode is actived when Vstdby is tied to GND

2. Dynamic measurements - 20*log(rms(Vout)/rms(Vripple)). Vripple is the surimposed sinus signal to Vcc @ f = 217Hz

Symbol	Parameter	Min.	Тур.	Max.	Unit
I _{CC}	Supply Current No input signal, no load		5.5	8	mA
ISTANDBY	Standby Current ¹⁾ No input signal, Vstdby = GND, RL = 8 Ω		10	1000	nA
Voo	Output Offset Voltage No input signal, RL = 8Ω		5	20	mV
Ро	Output Power THD = 1% Max, f = 1kHz, RL = 8Ω		300		mW
THD + N	Total Harmonic Distortion + Noise Po = 250mW rms, Gv = 2, 20Hz < f < 20kHz, RL = 8Ω		0.15		%
PSRR	Power Supply Rejection Ratio ²⁾ f = 217Hz, RL = 8Ω , RFeed = $22K\Omega$, Vripple = 200mV rms		77		dB
Φ_{M}	Phase Margin at Unity Gain $R_L = 8\Omega$, $C_L = 500pF$		70		Degrees
GM	Gain Margin $R_L = 8\Omega$, $C_L = 500pF$		20		dB
GBP	Gain Bandwidth Product $R_L = 8\Omega$		2		MHz

V _{CC} = +3.3V.	GND = 0V . T	- amb = 25°C	(unless	otherwise	specified) ³⁾
	$\mathbf{O} = \mathbf{O} \mathbf{I}, \mathbf{I}$		(01110000	011011000	opoomoa)

1. Standby mode is actived when Vstdby is tied to GND

2. Dynamic measurements - 20*log(rms(Vout)/rms(Vripple)). Vripple is the surimposed sinus signal to Vcc @ f = 217Hz

3. All electrical values are made by correlation between 2.6V and 5V measurements

ELECTRICAL CHARACTERISTICS

 $V_{CC} = 2.6V$, GND = 0V, $T_{amb} = 25^{\circ}C$ (unless otherwise specified)

Symbol	Parameter	Min.	Тур.	Max.	Unit
I _{CC}	Supply Current No input signal, no load		5.5	8	mA
ISTANDBY	Standby Current ¹⁾ No input signal, Vstdby = GND, RL = 8Ω		10	1000	nA
Voo	Output Offset Voltage No input signal, RL = 8Ω		5	20	mV
Po	Output Power THD = 1% Max, f = 1kHz, RL = 8Ω		180		mW
THD + N	Total Harmonic Distortion + Noise Po = 200mW rms, Gv = 2, 20Hz < f < 20kHz, RL = 8Ω		0.15		%
PSRR	Power Supply Rejection Ratio ²⁾ f = 217Hz, RL = 8Ω , RFeed = $22K\Omega$, Vripple = 200mV rms		77		dB
Φ_{M}	Phase Margin at Unity Gain $R_L = 8\Omega$, $C_L = 500pF$		70		Degrees
GM	Gain Margin $R_L = 8\Omega$, $C_L = 500 pF$		20		dB
GBP	Gain Bandwidth Product $R_L = 8\Omega$		2		MHz

1. Standby mode is actived when Vstdby is tied to GND

2. Dynamic measurements - 20*log(rms(Vout)/rms(Vripple)). Vripple is the surimposed sinus signal to Vcc @ f = 217Hz

Components	Functional Description				
Rin	Inverting input resistor which sets the closed loop gain in conjunction with Rfeed. This resistor also forms a high pass filter with Cin (fc = $1 / (2 \times Pi \times Rin \times Cin))$				
Cin	Input coupling capacitor which blocks the DC voltage at the amplifier input terminal				
Rfeed	Feed back resistor which sets the closed loop gain in conjunction with Rin				
Cs	Supply Bypass capacitor which provides power supply filtering				
Cb	Bypass pin capacitor which provides half supply filtering				
Cfeed	Low pass filter capacitor allowing to cut the high frequency (low pass filter cut-off frequency 1 / (2 x Pi x Rfeed x Cfeed))				
Rstb	Pull-up resistor which fixes the right supply level on the standby pin				
Gv	Closed loop gain in BTL configuration = 2 x (Rfeed / Rin)				

REMARKS

1. All measurements, except PSRR measurements, are made with a supply bypass capacitor $Cs = 100 \mu F$. **2.** The standby response time is about $1 \mu s$.

Fig. 1 : Open Loop Frequency Response



Fig. 3 : Open Loop Frequency Response



Fig. 5 : Open Loop Frequency Response



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Fig. 2 : Open Loop Frequency Response



Fig. 4 : Open Loop Frequency Response



Fig. 6 : Open Loop Frequency Response



Fig. 7 : Open Loop Frequency Response



Fig. 9 : Open Loop Frequency Response



Fig. 8 : Open Loop Frequency Response



Fig. 10 : Power Supply Rejection Ratio (PSRR) vs Power supply



Fig. 12 : Power Supply Rejection Ratio (PSRR) vs Bypass Capacitor







Fig. 11 : Power Supply Rejection Ratio (PSRR) vs Feedback Capacitor



Fig. 13 : Power Supply Rejection Ratio (PSRR) vs Input Capacitor





Fig. 15 : Pout @ THD + N = 1% vs Supply Voltage vs RL

Fig. 17 : Power Dissipation vs Pout







Fig. 16 : Pout @ THD + N = 10% vs Supply Voltage vs RL



Fig. 18 : Power Dissipation vs Pout



Fig. 20 : Power Derating Curves



Fig. 21 : Output Power vs Load Resistance



Fig. 23 : Clipping Voltage vs Supply Voltage







Fig. 22 : Output Power vs Load Resistance



Fig. 24 : Frequency response vs Cin & Cfeed



Fig. 26 : THD + N vs Output Power



Fig. 28 : THD + N vs Output Power



Fig. 30 : THD + N vs Output Power



Fig. 27 : THD + N vs Output Power



Fig. 29 : THD + N vs Output Power



Fig. 31 : THD + N vs Output Power



Fig. 32 : THD + N vs Output Power



Fig. 34 : THD + N vs Output Power



Fig. 36 : THD + N vs Output Power



Fig. 33 : THD + N vs Output Power



Fig. 35 : THD + N vs Output Power



Fig. 37 : THD + N vs Output Power



Fig. 38 : THD + N vs Output Power



Fig. 40 : THD + N vs Output Power



Fig. 42 : THD + N vs Output Power



Fig. 39 : THD + N vs Output Power



Fig. 41 : THD + N vs Output Power



Fig. 43 : THD + N vs Output Power





Fig. 44 : Signal to Noise Ratio vs Power Supply with Unweighted Filter (20Hz to 20kHz)









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Fig. 45 : Signal to Noise Ratio Vs Power Supply with Unweighted Filter (20Hz to 20kHz)



Fig. 47 : Signal to Noise Ratio vs Power Supply with Weighted Filter Type A



Fig. 49 : Current Consumption vs Standby Voltage @ Vcc = 5V



Fig. 50 : Current Consumption vs Standby Voltage @ Vcc = 3.3V



Fig. 51 : Current Consumption vs Standby Voltage @ Vcc = 2.6V



BTL Configuration Principle

The TS4902 is a monolithic power amplifier with a BTL (Bridge Tied Load) output configuration. BTL means that each end of the load is connected to two single ended output amplifiers. Thus, we have:

Single ended output 1 = Vout1 = Vout (V) Single ended output 2 = Vout2 = -Vout (V)

And Vout1 - Vout2 = 2Vout (V)

The output power is :

Pout =
$$\frac{(2 \text{ Vout}_{\text{RMS}})^2}{\text{R}_{\text{L}}}$$
 (W)

For the same power supply voltage, the output power in BTL configuration is four times higher than the output power in single ended configuration.

■ Gain In Typical Application Schematic (cf. page 1)

In flat region (no effect of Cin), the output voltage of the first stage is :

Vout1 =
$$-Vin \frac{Rfeed}{Rin} (V)$$

For the second stage : Vout2 = -Vout1 (V)

The differential output voltage is

Vout2 - Vout1 = 2Vin
$$\frac{Rfeed}{Rin}$$
 (V)

The differential gain named gain (Gv) for more convenient usage is :

$$Gv = \frac{Vout2 - Vout1}{Vin} = 2 \frac{Rfeed}{Rin}$$

Remark : Vout2 is in phase with Vin and Vout1 is 180 phased with Vin. It means that the positive terminal of the loudspeaker should be connected to Vout2 and the negative to Vout1.

Low and high frequency response

In low frequency region, the effect of Cin starts. Cin with Rin forms a high pass filter with a -3dB cut off frequency

$$F_{CL} = \frac{1}{2\pi \operatorname{Rin} \operatorname{Cin}} (H_z)$$

In high frequency region, you can limit the bandwidth by adding a capacitor (Cfeed) in parallel with Rfeed. Its form a low pass filter with a -3dB cut off frequency

$$F_{CH} = \frac{1}{2\pi \text{ Rfeed Cfeed}} (Hz)$$

Power dissipation and efficiency

Hypothesis :

• Voltage and current in the load are sinusoidal (Vout and lout)

Supply voltage is a pure DC source (Vcc)

Regarding the load we have :

$$VOUT = V_{PEAK} \sin \omega t (V)$$

and

$$\mathsf{IOUT} = \frac{\mathsf{VOUT}}{\mathsf{RL}} (\mathsf{A})$$

and

$$\mathsf{POUT} = \frac{\mathsf{VPEAK}^2}{2\mathsf{RL}} (\mathsf{W})$$

Then, the average current delivered by the supply voltage is:

$$ICC_{AVG} = 2 \frac{VPEAK}{\pi RL} (A)$$

The power delivered by the supply voltage is $Psupply = Vcc Icc_{AVG}$ (W)

Then, the **power dissipated by the amplifier** is Pdiss = Psupply - Pout (W)

$$\mathsf{Pdiss} = \frac{2\sqrt{2\mathsf{Vcc}}}{\pi\sqrt{\mathsf{RL}}}\sqrt{\mathsf{POUT}} - \mathsf{POUT} (\mathsf{W})$$

and the maximum value is obtained when

$$\frac{\partial \mathsf{Pdiss}}{\partial \mathsf{POUT}} = 0$$

and its value is:

$$Pdissmax = \frac{2 Vcc^2}{\pi^2 R_1} (W)$$

Remark : This maximum value is only depending on power supply voltage and load values.

The **efficiency** is the ratio between the output power and the power supply

$$\eta = \frac{\text{POUT}}{\text{Psupply}} = \frac{\pi \text{VPEAK}}{4 \text{Vcc}}$$

The maximum theoretical value is reached when Vpeak = Vcc, so

$$\frac{\pi}{4} = 78.5\%$$

Decoupling of the circuit

Two capacitors are needed to bypass properly the TS4902, a power supply bypass capacitor Cs and a bias voltage bypass capacitor Cb.

Cs has especially an influence on the THD+N in high frequency (above 7kHz) and indirectly on the power supply disturbances.

With $100\mu F$, you can expect similar THD+N performances like shown in the datasheet.

If Cs is lower than 100μ F, in high frequency increases, THD+N and disturbances on the power supply rail are less filtered.

To the contrary, if Cs is higher than 100μ F, those disturbances on the power supply rail are more filtered.

Cb has an influence on THD+N in lower frequency, but its function is critical on the final result of PSRR with input grounded in lower frequency.

If Cb is lower than 1 μ F, THD+N increase in lower frequency (see THD+N vs frequency curves) and the PSRR worsens up

If Cb is higher than 1μ F, the benefit on THD+N in lower frequency is small but the benefit on PSRR is substantial (see PSRR vs. Cb curve : fig.12).

Note that Cin has a non-negligible effect on PSRR in lower frequency. Lower is its value, higher is the PSRR (see fig. 13).

Pop and Click performance

Pop and Click performance is intimately linked with the size of the input capacitor Cin and the bias voltage bypass capacitor Cb.

Size of Cin is due to the lower cut-off frequency and PSRR value requested. Size of Cb is due to THD+N and PSRR requested always in lower frequency. Moreover, Cb determines the speed that the amplifier turns ON. The slower the speed is, the softer the turn ON noise is.

The charge time of Cb is directly proportional to the internal generator resistance $50k\Omega$.

Then, the charge time constant for Cb is

$\tau \mathbf{b} = \mathbf{50k} \Omega \mathbf{xCb} (s)$

As Cb is directly connected to the non-inverting input (pin 2 & 3) and if we want to minimize, in amplitude and duration, the output spike on Vout1 (pin 5), Cin must be charged faster than Cb. The charge time constant of Cin is

 τ in = (Rin+Rfeed)xCin (s)

Thus we have the relation τ **in** << τ **b** (s)

The respect of this relation permits to minimize the pop and click noise.

Remark : Minimize Cin and Cb has a benefit on pop and click phenomena but also on cost and size of the application.

Example : your target for the -3dB cut off frequency is 100 Hz. With Rin=Rfeed=22 k Ω , Cin=72nF (in fact 82nF or 100nF).

With Cb=1 μ F, if you choose the one of the latest two values of Cin, the pop and click phenomena at power supply ON or standby function ON/OFF will be very small

 $50 \text{ k}\Omega x 1\mu \text{F} >> 44 \text{k}\Omega x 100 \text{nF}$ (50 ms >> 4.4 ms). Increasing Cin value increases the pop and click

phenomena to an unpleasant sound at power supply ON and standby function ON/OFF.

Why Cs is not important in pop and click consideration ?

Hypothesis :

- Cs = 100µF
- Supply voltage = 5V
- Supply voltage internal resistor = 0.1Ω
- Supply current of the amplifier Icc = 6mA

At power ON of the supply, the supply capacitor is charged through the internal power supply resistor. So, to reach 5V you need about five to ten times the charging time constant of Cs (τ s = 0.1xCs (s)).

Then, this time equal 50µs to $100µs \ll \tau b$ in the majority of application.

At power OFF of the supply, Cs is discharged by a constant current lcc. The discharge time from 5V to 0V of Cs is

$$tDischCs = \frac{5Cs}{Icc} = 83 ms$$

Now, we must consider the discharge time of Cb. At power OFF or standby ON, Cb is discharged by a 100k Ω resistor. So the discharge time is about $\tau b_{Disch} \approx 3xCbx100k\Omega$ (s).

In the majority of application, Cb=1 μ F, then $\tau b_{Disch} \approx 300 ms >> t_{dischCs}$.

■ How to use the PSRR curves (page 7)

We have finished a design and we have chosen the components values :

• Rin=Rfeed=22k Ω , Cin=100nF, Cb=1 μ F

Now, on fig. 13, we can see the PSRR (input grounded) vs frequency curves. At 217Hz we have a PSRR value of -36dB.

In fact, we want a value of about -70dB. So, we need a gain of +34dB !

Now, on fig. 12 we can see the effect of Cb on the PSRR (input grounded) vs. frequency. With $Cb=100\mu F$, we can reach the -70dB value.

The process to obtain the final curve (Cb=100 μ F, Cin=100nF, Rin=Rfeed=22k Ω) is a simple transfer point by point on each frequency of the curve on fig. 13 to the curve on fig. 12.

The measurement result is shown on figure A.





Remark on PSRR measurement conditions

What is the PSRR ?

The PSRR is the Power Supply Rejection Ratio. It's a kind of SVR in a determined frequency range. The PSRR of a device is the ratio between the power supply disturbance and the result on the output. We can say that the PSRR is the ability of a device to minimize the impact of power supply disturbances to the output.

How do we measure the PSRR ?



Fig. B : PSRR measurement schematic

Measurement process:

- Fix the DC voltage supply (Vcc)
- Fix the AC sinusoidal ripple voltage (Vripple)
- No bypass capacitor Cs is used

The PSRR value for each frequency is :

$$PSRR(dB) = 20 \times Log_{10} \left[\frac{Rms(Vripple)}{Rms(Vs_{+} - Vs_{-})} \right]$$

Remark : The measurement of the RMS voltage is not a selective RMS measurement but a full range (2 Hz to 125 kHz) RMS measurement. This means we have: the effective RMS signal + the noise.

PACKAGE MECHANICAL DATA

8 PINS - PLASTIC MICROPACKAGE (SO)



Dim		Millimeters			Inches		
Diin.	Min.	Тур.	Max.	Min.	Тур.	Max.	
A			1.75			0.069	
a1	0.1		0.25	0.004		0.010	
a2			1.65			0.065	
a3	0.65		0.85	0.026		0.033	
b	0.35		0.48	0.014		0.019	
b1	0.19		0.25	0.007		0.010	
С	0.25		0.5	0.010		0.020	
c1			45°	(typ.)			
D	4.8		5.0	0.189		0.197	
E	5.8		6.2	0.228		0.244	
е		1.27			0.050		
e3		3.81			0.150		
F	3.8		4.0	0.150		0.157	
L	0.4		1.27	0.016		0.050	
М			0.6			0.024	
S			8° (max.)			

PACKAGE MECHANICAL DATA

8 PINS - PLASTIC MICROPACKAGE (miniSO)



Dim.	Millimeters				Inches	
	Min.	Тур.	Max.	Min.	Тур.	Max.
A			1.100			0.043
A1	0.050	0.100	0.150	0.002	0.004	0.006
A2	0.780	0.860	0.940	0.031	0.034	0.037
b	0.250	0.330	0.400	0.010	0.013	0.016
С	0.130	0.180	0.230	0.005	0.007	0.009
D	2.900	3.000	3.100	0.114	0.118	0.122
E	4.750	4.900	5.050	0.187	0.193	0.199
E1	2.900	3.000	3.100	0.114	0.118	0.122
е		0.650			0.026	
L	0.400	0.550	0.700	0.016	0.022	0.028
L1		0.950			0.037	
k	0d	3d	6d	0d	3d	6d
CCC			0.100			0.004

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